

The OHDP42CB is a high-output, high-speed silicon photodiode mounted in durable hermetically sealed TO-8F metal can package, which provides years of reliable performance even under demanding conditions such as use outdoors.

FEATURES

- High-output power.
- High-speed response
- Durable

APPLICATIONS

- Infrared sensors
- Optical detectors
- UV detectors



ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

Item	Symbol	Cond.	Min.	Typ.	Max.	Unit
Open circuit voltage	Voc	Ev=1,000Lux		0.4		V
Short circuit current	Isc			190.0		μA
Dark current	Id	VR=5V			0.1	μA
Curve factor	C.F		0.55			—
Capacitance	Ct	V=0V, f=1MHZ		1,050		PF
Temperature coefficient of Voc	α t			-2.2		mV/°C
Temperature coefficient of isc	β t			0.18		%/°C
Spectral sensitivity	λ		450~1,050			nm
Peak wavelength	λp			900		nm
Half angle	Δ θ			±60		deg.

MAXIMUM RATINGS

(Ta=25°C)

Item	Symbol	Rating	Unit
Reverse voltage	VR	10	V
Operating temp.	Topr.	-20~+100	°C
Storage temp.	Tstg.	-30~+100	°C
Soldering temp. ⁽¹⁾	Tsol.	260	°C

(1)For MAX.5seconds at the position of 2mm from the package

